

1826  
ED

**C<sub>4</sub>H<sub>10</sub>SSi**

**3,3-Dimethyl-1-thia-3-silacyclobutane**

**C<sub>s</sub>**

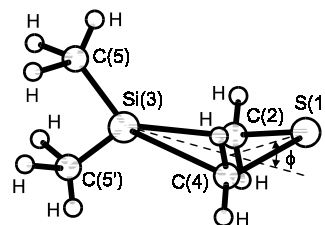
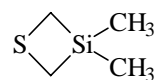
$r_a$	Å <sup>a)</sup>	$\theta_\alpha$	deg <sup>a)</sup>
S–C	1.853(4)	C(5)–Si–C(5')	106.9(7)
Si–C(5,5')	1.870(5)	C(2)–Si–C(4)	86.1(3)
Si–C(2,4)	1.916(3)	Si–C–S	90.5(5)
C–H	1.086(3)	C–S–C	89.5(4)
		H–C(5,5')–H	109 <sup>b)</sup>
		H–C(2,4)–H	112 <sup>b)</sup>
		$\phi$ <sup>c)</sup>	20.3(20)

The nozzle temperature was 35(10) °C.

<sup>a)</sup> Three times the estimated standard errors.

<sup>b)</sup> Assumed.

<sup>c)</sup> Angle between the CSiC and CSC planes.



Mastryukov, V.S., Strelkov, S.A., Golubinskii, A.V., Vilkov, L.V., Khristenko, L.V., Krasnoshchekov, S.V., Pentin, Yu.A., Kirpichenko, S.V., Suslova, E.N., Voronkov, M.G.: Zh. Strukt. Khim. **28** No.5 (1987) 49; Russ. J. Struct. Chem. (Engl. Transl.) **28** (1987) 674.  
See also: Mastryukov, V.S., Strelkov, S.A., Golubinskii, A.V., Vilkov, L.V., Kirpichenko, S.V., Suslova, E.N., Voronkov, M.G.: Dokl. Akad. Nauk SSSR **271** (1983) 384.